Product Preview

400 MHz Current Feedback Op Amp with Enable Feature

NCS2511 is a 400 MHz current feedback monolithic operational amplifier featuring high slew rate and low differential gain and phase error. The current feedback architecture allows for a superior bandwidth and low power consumption. This device features an enable pin.

Features

- -3.0 dB Small Signal BW (A_V = +2.0, V_O = 0.5 V_{p-p}) 400 MHz Typ
- Slew Rate 600 V/us
- Supply Current 5.0 mA
- Input Referred Voltage Noise 6.0 nV/ $\sqrt{\text{Hz}}$
- THD -60 dBc (f = 5.0 MHz, $V_0 = 2.0 V_{p-p}$)
- Output Current 150 mA

- Pin Compatible with AD8001
 Pb-Free Packers

Applications

- High Resolution Video
- Line Driver
- High-Speed Instrumentation
- Wide Dynamic Range IF Amp
- Set Top Box
- NTSC/PAL/HDTV

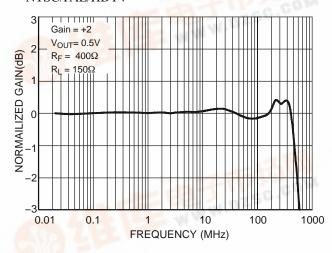


Figure 1. Frequency Response: Gain (dB) vs. Frequency Av = +2.0

This document contains information on a product under development. ON Semiconductor serves the right to change or discontinue this product without notice.



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MARKING DIAGRAMS



SO-8 **D SUFFIX CASE 751**





SOT23-6 (TSOP-6) **SN SUFFIX CASE 318G**



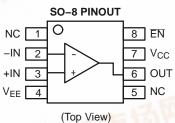
YB1, N2511 = NCS2511

= Assembly Location

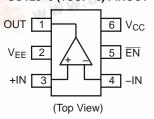
= Wafer Lot = Year

= Work Week W

= Pb-Free Package



SOT23-6 (TSOP-6) PINOUT



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 11 of this data sheet.

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PIN FUNCTION DESCRIPTION

Pin (SO-8)	Pin (SOT23/SC70)	Symbol	Function	Equivalent Circuit
6	1	OUT	Output	V _{CC} ESD OUT V _{EE}
4	2	V _{EE}	Negative Power Supply	
3	3	+IN	Non-inverted Input	V _{CC} +IN V _{EE}
2	4	-IN	Inverted Input	See Above
7	6	V_{CC}	Positive Power Supply	
8	5	ĒN	Enable	EN ESD VEE
1, 8	N/A	NC	No Connect	

ENABLE PIN TRUTH TABLE

	High	Low*
Enable	Disabled	Enabled

^{*}Default open state

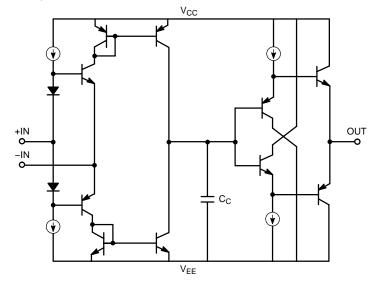


Figure 2. Simplified Device Schematic

ATTRIBUTES

Charac	Value	
ESD Human Body Model Machine Model Charged Device Model		2.0 kV (Note 1) 200 V 1.0 kV
Moisture Sensitivity (No	te 2)	Level 1
Flammability Rating	UL 94 V-0 @ 0.125 in	

- 1. 0.8 kV between the input pairs +IN and -IN pins only. All other pins are 2.0 kV.
- 2. For additional information, see Application Note AND8003/D.

MAXIMUM RATINGS

Parameter	Symbol	Rating	Unit
Power Supply Voltage	V _S	11	Vdc
Input Voltage Range	VI	≤V _S	Vdc
Input Differential Voltage Range	V _{ID}	≤V _S	Vdc
Output Current	lo	100	mA
Maximum Junction Temperature (Note 3)	TJ	150	°C
Operating Ambient Temperature	T _A	-40 to +85	°C
Storage Temperature Range	T _{stg}	-60 to +150	°C
Power Dissipation	P _D	(See Graph)	mW
Thermal Resistance, Junction–to–Air SO–8 SOT23–6	$R_{ heta JA}$	139 121	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

3. Power dissipation must be considered to ensure maximum junction temperature (T,j) is not exceeded.

MAXIMUM POWER DISSIPATION

The maximum power that can be safely dissipated is limited by the associated rise in junction temperature. For the plastic packages, the maximum safe junction temperature is 150°C. If the maximum is exceeded momentarily, proper circuit operation will be restored as soon as the die temperature is reduced. Leaving the device in the "overheated" condition for an extended period can result in device damage. To ensure proper operation, it is important to observe the derating curves.

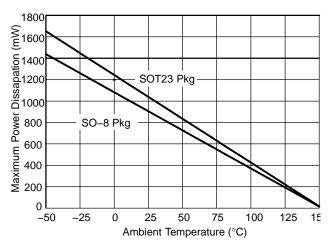


Figure 3. Power Dissipation vs. Temperature

AC ELECTRICAL CHARACTERISTICS (V_{CC} = +5.0 V, V_{EE} = -5.0 V, T_A = -40°C to +85°C, R_L = 150 Ω to GND, R_F = 400 Ω , A_V = +2.0, Enable is left open, unless otherwise specified).

Symbol	Characteristic	Conditions	Min	Тур	Max	Unit
FREQUENC	CY DOMAIN PERFORMANCE					
BW	Bandwidth 3.0 dB Small Signal 3.0 dB Large Signal	$A_V = +2.0, V_O = 0.5 V_{p-p}$ $A_V = +2.0, V_O = 2.0 V_{p-p}$		400 300		MHz
GF _{0.1dB}	0.1 dB Gain Flatness Bandwidth	A _V = +2.0		100		MHz
dG	Differential Gain	$A_V = +2.0, R_L = 150 \Omega, f = 3.58 MHz$		0.01		%
dP	Differential Phase	$A_V = +2.0, R_L = 150 \Omega, f = 3.58 MHz$		0.01		0
TIME DOM	AIN RESPONSE					
SR	Slew Rate	$A_V = +2.0, V_{step} = 2.0 V$		600		V/μs
t _s	Settling Time 0.01% 0.1%	$A_V = +2.0, V_{step} = 2.0 V$ $A_V = +2.0, V_{step} = 2.0 V$		9.0 7.0		ns
t _r t _f	Rise and Fall Time	$(10\%-90\%) A_V = +2.0, V_{step} = 2.0 V$		1.5		ns
t _{ON}	Turn-on Time			55		ns
t _{OFF}	Turn-off Time			55		ns
HARMONIC	/NOISE PERFORMANCE					
THD	Total Harmonic Distortion	$f = 5.0 \text{ MHz}, V_O = 2.0 V_{p-p}$		-60		dBc
HD2	2nd Harmonic Distortion	$f = 5.0 \text{ MHz}, V_O = 2.0 V_{p-p}$		-62		dBc
HD3	3rd Harmonic Distortion	$f = 5.0 \text{ MHz}, V_O = 2.0 V_{p-p}$		-66		dBc
IP3	Third-Order Intercept	$f = 10 \text{ MHz}, V_O = 1.0 V_{p-p}$		35		dBm
SFDR	Spurious-Free Dynamic Range	$f = 5.0 \text{ MHz}, V_O = 2.0 V_{p-p}$		55		dBc
e _N	Input Referred Voltage Noise	f = 1.0 MHz		6.0		nV/√Hz
i _N	Input Referred Current Noise	f = 1.0 MHz, Inverting f = 1.0 MHz, Non-Inverting		10 3.0		pA/√ Hz

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DC ELECTRICAL CHARACTERISTICS (V_{CC} = +5.0 V, V_{EE} = -5.0 V, T_A = -40°C to +85°C, R_L = 150 Ω to GND, R_F = 400 Ω , A_V = +2.0, Enable is left open, unless otherwise specified).

Symbol	Characteristic	Conditions	Min	Тур	Max	Unit
DC PERFO	RMANCE					
V _{IO}	Input Offset Voltage		-5.0	0	+5.0	mV
$\Delta V_{IO}/\Delta T$	Input Offset Voltage Temperature Coefficient			6.0		μV/°C
I _{IB}	Input Bias Current	+Input (Non-Inverting), $V_O = 0 \text{ V}$ -Input (Inverting), $V_O = 0 \text{ V}$ (Note 4)		±3.0 ±6.0		μА
$\Delta I_{\text{IB}}/\Delta T$	Input Bias Current Temperature Coefficient	+Input (Non-Inverting), $V_O = 0 \text{ V}$ -Input (Inverting), $V_O = 0 \text{ V}$		+40 -10		nA/°C
V_{IH}	Input High Voltage (Enable) (Note 4)		2.5			V
V _{IL}	Input Low Voltage (Enable) (Note 4)				-2.5	V
INPUT CHA	RACTERISTICS					
V _{CM}	Input Common Mode Voltage Range			±3.0		V
CMRR	Common Mode Rejection Ratio	(See Graph)		55		dB
R _{IN}	Input Resistance	+Input (Non-Inverting) -Input (Inverting)		100 50		kΩ Ω
C _{IN}	Differential Input Capacitance			1.0		pF
OUTPUT C	HARACTERISTICS			•		
R _{OUT}	Output Resistance	$A_V = +2.0, V_O = 0.5 V, f = 5.0 MHz$		0.1		Ω
Vo	Output Voltage Range			±3.0		V
Io	Output Current		±90	±120		mA
POWER SU	JPPLY					
Vs	Operating Voltage Supply Range			10		V
I _{S,ON}	Power Supply Current – Enabled	V _O = 0 V		5.0		mA
I _{S,OFF}	Power Supply Current – Disabled	V _O = 0 V		0.1		mA
PSRR	Power Supply Rejection Ratio	(See Graph)		60		dB

^{4.} Guaranteed by design and/or characterization.

AC ELECTRICAL CHARACTERISTICS (V_{CC} = +2.5 V, V_{EE} = -2.5 V, T_A = -40°C to +85°C, R_L = 150 Ω to GND, R_F = 400 Ω , A_V = +2.0, Enable is left open, unless otherwise specified).

Symbol	Characteristic	Conditions	Min	Тур	Max	Unit
FREQUENC	CY DOMAIN PERFORMANCE			•		•
BW	Bandwidth 3.0 dB Small Signal 3.0 dB Large Signal	$A_V = +2.0, V_O = 0.5 V_{p-p}$ $A_V = +2.0, V_O = 1.0 V_{p-p}$		300 200		MHz
GF _{0.1dB}	0.1 dB Gain Flatness Bandwidth	A _V = +2.0		750		MHz
dG	Differential Gain	$A_V = +2.0, R_L = 150 \Omega, f = 3.58 MHz$		0.01		%
dP	Differential Phase	$A_V = +2.0, R_L = 150 \Omega, f = 3.58 MHz$		0.01		0
TIME DOM	AIN RESPONSE					
SR	Slew Rate	$A_V = +2.0, V_{step} = 1.0 V$		400		V/μs
t _s	Settling Time 0.01% 0.1%	$A_V = +2.0, V_{step} = 1.0 V$ $A_V = +2.0, V_{step} = 1.0 V$		12 9.0		ns
t _r t _f	Rise and Fall Time	$(10\%-90\%) A_V = +2.0, V_{step} = 1.0 V$		2.0		ns
t _{ON}	Turn-on Time			55		ns
t _{OFF}	Turn-off Time			55		ns
HARMONIC	/NOISE PERFORMANCE					
THD	Total Harmonic Distortion	$f = 5.0 \text{ MHz}, V_O = 1.0 V_{p-p}$		-60		dBc
HD2	2nd Harmonic Distortion	$f = 5.0 \text{ MHz}, V_O = 1.0 V_{p-p}$		-62		dBc
HD3	3rd Harmonic Distortion	$f = 5.0 \text{ MHz}, V_O = 1.0 V_{p-p}$		-66		dBc
IP3	Third-Order Intercept	$f = 10 \text{ MHz}, V_O = 0.5 V_{p-p}$		35		dBm
SFDR	Spurious-Free Dynamic Range	$f = 5.0 \text{ MHz}, V_O = 1.0 V_{p-p}$		55		dBc
e _N	Input Referred Voltage Noise	f = 1.0 MHz		6.0		nV/√ Hz
i _N	Input Referred Current Noise	f = 1.0 MHz, Inverting f = 1.0 MHz, Non–Inverting		10 3.0		pA/√ Hz

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DC ELECTRICAL CHARACTERISTICS (V_{CC} = +2.5 V, V_{EE} = -2.5 V, T_A = -40°C to +85°C, R_L = 150 Ω to GND, R_F = 400 Ω , A_V = +2.0, Enable is left open, unless otherwise specified).

Symbol	Characteristic	Conditions	Min	Тур	Max	Unit
DC PERFO	RMANCE			•	•	•
V _{IO}	Input Offset Voltage		-5.0	0	+5.0	mV
$\Delta V_{IO}/\Delta T$	Input Offset Voltage Temperature Coefficient			6.0		μV/°C
I _{IB}	Input Bias Current	+Input (Non-Inverting), $V_O = 0 \text{ V}$ -Input (Inverting), $V_O = 0 \text{ V}$ (Note 5)		±3.0 ±6.0		μΑ
$\Delta I_{\text{IB}}/\Delta T$	Input Bias Current Temperature Coefficient	+Input (Non-Inverting), $V_O = 0 \text{ V}$ -Input (Inverting), $V_O = 0 \text{ V}$		+40 -10		nA/°C
V_{IH}	Input High Voltage (Enable) (Note 5)		1.875			V
V_{IL}	Input Low Voltage (Enable) (Note 5)				-1.875	V
NPUT CHA	RACTERISTICS			•	•	•
V _{CM}	Input Common Mode Voltage Range			±1.2		V
CMRR	Common Mode Rejection Ratio	(See Graph)		55		dB
R _{IN}	Input Resistance	+Input (Non-Inverting) -Input (Inverting)		100 50		kΩ Ω
C _{IN}	Differential Input Capacitance			1.0		pF
OUTPUT C	HARACTERISTICS			•		•
R _{OUT}	Output Resistance	$A_V = +2.0, V_O = 0.5 V, f = 5.0 MHz$		0.1		Ω
Vo	Output Voltage Range			±1.0		V
I _O	Output Current		±90	±120		mA
POWER SU	JPPLY					
Vs	Operating Voltage Supply Range			5.0		V
I _{S,ON}	Power Supply Current – Enabled	V _O = 0 V		5.0		mA
I _{S,OFF}	Power Supply Current – Disabled	V _O = 0 V		0.1		mA
PSRR	Power Supply Rejection Ratio	(See Graph)		60		dB

^{5.} Guaranteed by design and/or characterization.

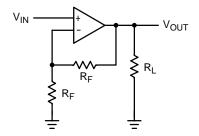


Figure 4. Typical Test Setup (A_V = +2.0, R_F = 400 Ω , R_L = 150 Ω)

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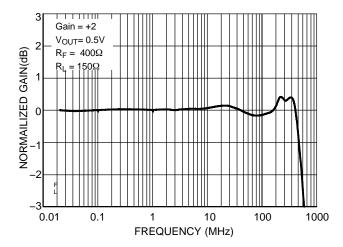


Figure 5. Frequency Response: Gain (dB) vs. Frequency Av = +2.0

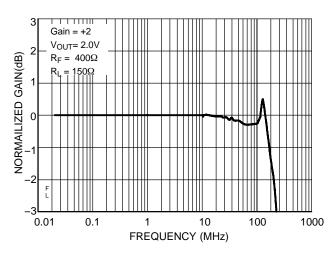


Figure 6. Large Signal Frequency Response Gain (dB) vs. Frequency

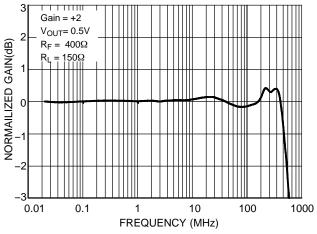


Figure 7. Small Signal Frequency Response Gain (dB) vs. Frequency

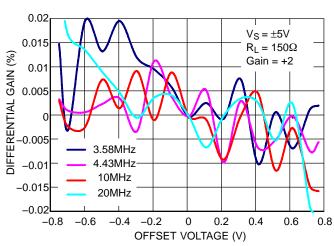


Figure 8. Differential Gain

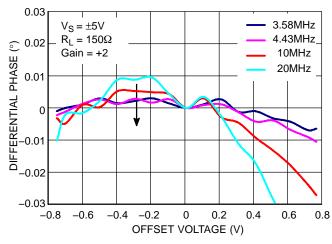


Figure 9. Differential Phase

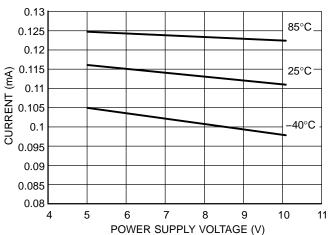


Figure 10. Supply Current vs. Power Supply (Enabled)

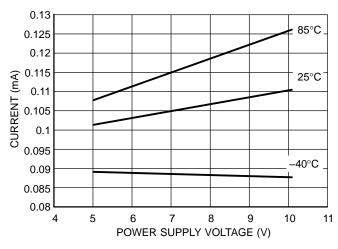


Figure 11. Supply Current vs. Power Supply (Disabled)

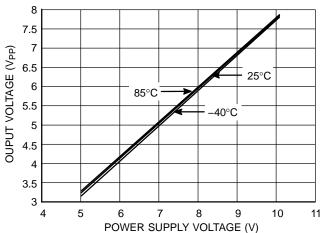


Figure 12. Output Voltage Swing vs. Supply Voltage

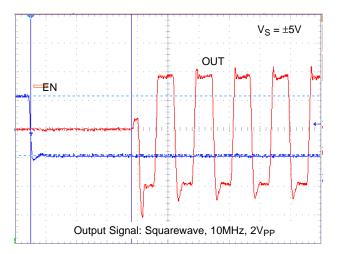


Figure 13. Turn ON Time Delay Vertical: 500mV/div Horizontal: 200ps

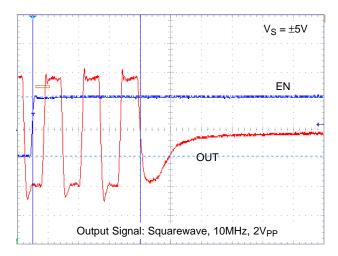


Figure 14. Turn OFF Time Delay Vertical: 500mV/div Horizontal: 200ps

General Design Considerations

The current feedback amplifier is optimized for use in high performance video and data acquisition systems. For current feedback architecture, its closed—loop bandwidth depends on the value of the feedback resistor. The closed—loop bandwidth is not a strong function of gain, as is for a voltage feedback amplifier, as shown in Figure 15.

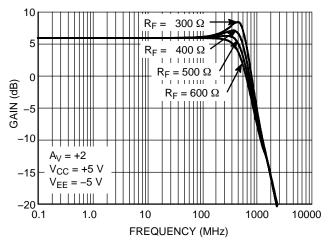


Figure 15. Frequency Response vs. R_F

The -3.0 dB bandwidth is, to some extent, dependent on the power supply voltages. By using lower power supplies, the bandwidth is reduced, because the internal capacitance increases. Smaller values of feedback resistor can be used at lower supply voltages, to compensate for this affect.

Feedback and Gain Resistor Selection for Optimum Frequency Response

A current feedback operational amplifier's key advantage is the ability to maintain optimum frequency response independent of gain by using appropriate values for the feedback resistor. To obtain a very flat gain response, the feedback resistor tolerance should be considered as well. Resistor tolerance of 1% should be used for optimum flatness. Normally, lowering RF resistor from its recommended value will peak the frequency response and extend the bandwidth while increasing the value of RF resistor will cause the frequency response to roll off faster. Reducing the value of RF resistor too far below its recommended value will cause overshoot, ringing, and eventually oscillation.

Since each application is slightly different, it is worth some experimentation to find the optimal RF for a given circuit. A value of the feedback resistor that produces $\sim 0.1 \text{ dB}$ of peaking is the best compromise between stability and maximal bandwidth. It is not recommended to

use a current feedback amplifier with the output shorted directly to the inverting input.

Printed Circuit Board Layout Techniques

Proper high speed PCB design rules should be used for all wideband amplifiers as the PCB parasitics can affect the overall performance. Most important are stray capacitances at the output and inverting input nodes as it can effect peaking and bandwidth. A space (3/16" is plenty) should be left around the signal lines to minimize coupling. Also, signal lines connecting the feedback and gain resistors should be short enough so that their associated inductance does not cause high frequency gain errors. Line lengths less than 1/4" are recommended.

Video Performance

This device designed to provide good performance with NTSC, PAL, and HDTV video signals. Best performance is obtained with back terminated loads as performance is degraded as the load is increased. The back termination reduces reflections from the transmission line and effectively masks transmission line and other parasitic capacitances from the amplifier output stage.

ESD Protection

All device pins have limited ESD protection using internal diodes to power supplies as specified in the attributes table (see Figure 16). These diodes provide moderate protection to input overdrive voltages above the supplies. The ESD diodes can support high input currents with current limiting series resistors. Keep these resistor values as low as possible since high values degrade both noise performance and frequency response. Under closed—loop operation, the ESD diodes have no effect on circuit performance. However, under certain conditions the ESD diodes will be evident. If the device is driven into a slewing condition, the ESD diodes will clamp large differential voltages until the feedback loop restores closed—loop operation. Also, if the device is powered down and a large input signal is applied, the ESD diodes will conduct.

NOTE: Human Body Model for +IN and -IN pins are rated at 0.8kV while all other pins are rated at 2.0kV.

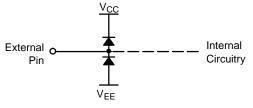


Figure 16. Internal ESD Protection

ORDERING INFORMATION

Device	Package	Shipping [†]
NCS2511SNT2	SOT23-6 (TSOP-6)	3000 Tape & Reel
NCS2511SNT2G	SOT23-6 (TSOP-6) (Pb-Free)	3000 Tape & Reel
NCS2511D*	SO-8	98 Units/Rail
NCS2511DG*	SO-8 (Pb-Free)	98 Units/Rail
NCS2511DR2*	SO-8	2500 Tape & Reel
NCS2511DR2G*	SO-8 (Pb-Free)	2500 Tape & Reel

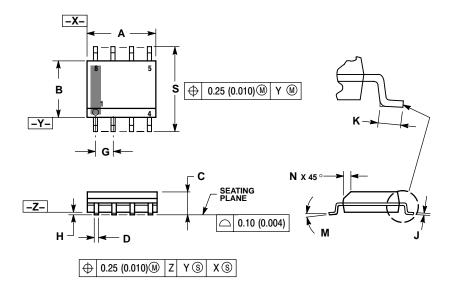
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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^{*}Contact ON Semiconductor for ordering information.

PACKAGE DIMENSIONS

SO-8 **D SUFFIX** CASE 751-07 **ISSUE AG**



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.

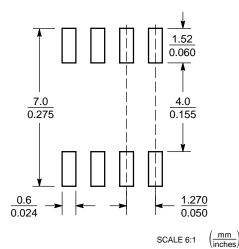
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- PER SIDE.

 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

 6. 751–01 THRU 751–06 ARE OBSOLETE. NEW STANDARD IS 751–07.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.80	5.00	0.189	0.197	
В	3.80	4.00	0.150	0.157	
U	1.35	1.75	0.053	0.069	
D	0.33	0.51	0.013	0.020	
G	1.27	7 BSC	0.050 BSC		
Η	0.10	0.25	0.004	0.010	
7	0.19	0.25	0.007	0.010	
K	0.40	1.27	0.016	0.050	
М	0 °	8 °	0 °	8 °	
N	0.25	0.50	0.010	0.020	
S	5.80	6.20	0.228	0.244	

SOLDERING FOOTPRINT*

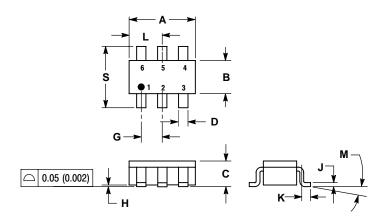


*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOT23-6 (TSOP-6) SN SÚFFIX

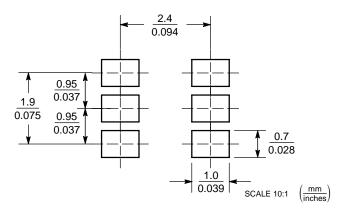
CASE 318G-02 ISSUE M



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	2.90	3.10	0.1142	0.1220	
В	1.30	1.70	0.0512	0.0669	
С	0.90	1.10	0.0354	0.0433	
D	0.25	0.50	0.0098	0.0197	
G	0.85	1.05	0.0335	0.0413	
Н	0.013	0.100	0.0005	0.0040	
J	0.10	0.26	0.0040	0.0102	
K	0.20	0.60	0.0079	0.0236	
L	1.25	1.55	0.0493	0.0610	
М	0 °	10 °	0 °	10°	
S	2.50	3.00	0.0985	0.1181	

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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